

DESCRIPTION

Monolithic temperature and overload protected logic level power MOSFET in **TOPFET2** technology assembled in a 3 pin plastic package.

APPLICATIONS

General purpose switch for driving

- lamps
- motors
- solenoids
- heaters

in automotive systems and other applications.

FEATURES

- TrenchMOS output stage
- Current limiting
- Overload protection
- Overtemperature protection
- Protection latched reset by input
- 5 V logic compatible input level
- Control of output stage and supply of overload protection circuits derived from input
- Low operating input current permits direct drive by micro-controller
- ESD protection on all pins
- Overvoltage clamping for turn off of inductive loads

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Continuous drain source voltage	50	V
I_D	Continuous drain current	8	A
P_D	Total power dissipation	40	W
T_j	Continuous junction temperature	150	°C
$R_{DS(ON)}$	Drain-source on-state resistance	100	mΩ
I_{ISL}	Input supply current $V_{IS} = 5\text{ V}$	650	μA

FUNCTIONAL BLOCK DIAGRAM

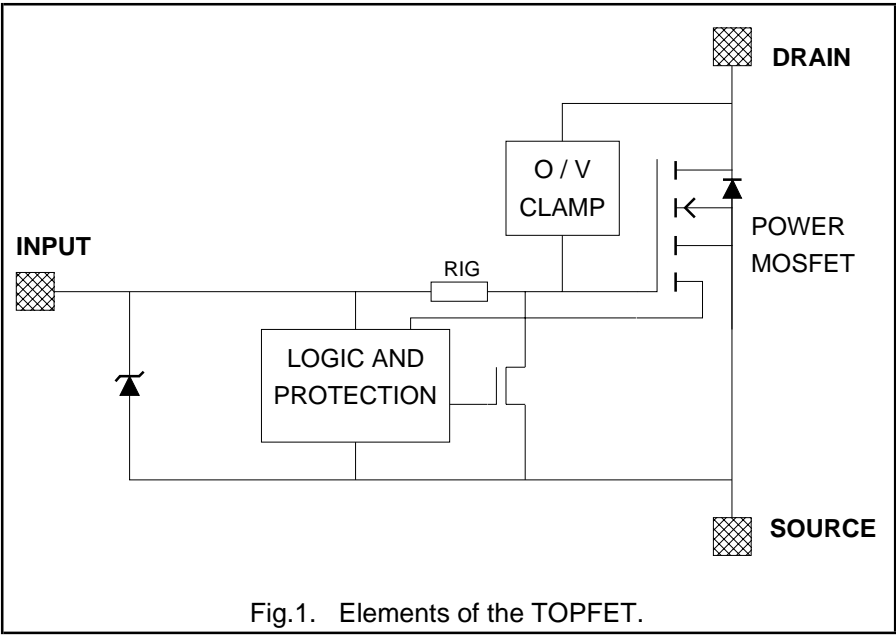
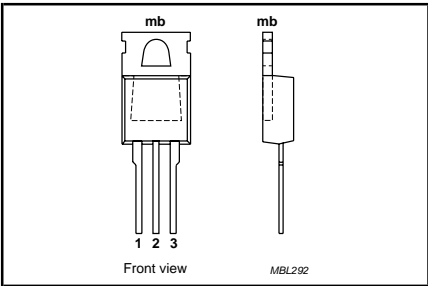


Fig.1. Elements of the TOPFET.

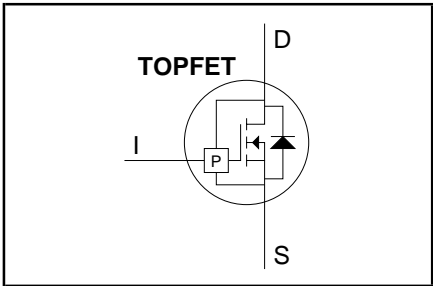
PINNING - SOT78B

PIN	DESCRIPTION
1	input
2	drain
3	source
tab	drain

PIN CONFIGURATION



SYMBOL



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BUK117-50DL

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Continuous drain source voltage ¹	-	-	50	V
I_D	Continuous drain current	$V_{IS} = 5\text{ V}; T_{mb} = 25\text{ °C}$	-	self - limited	A
I_D	Continuous drain current	$V_{IS} = 5\text{ V}; T_{mb} \leq 110\text{ °C}$	-	8	A
I_I	Continuous input current	-	-5	5	mA
I_{IRM}	Non-repetitive peak input current	$t_p \leq 1\text{ ms}$	-10	10	mA
P_D	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	40	W
T_{stg}	Storage temperature	-	-55	175	°C
T_j	Continuous junction temperature ²	normal operation	-	150	°C
T_{sld}	Lead temperature	during soldering	-	260	°C

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage	Human body model; $C = 250\text{ pF}; R = 1.5\text{ k}\Omega$	-	2	kV

OVERVOLTAGE CLAMPING LIMITING VALUES

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
E_{DSM}	Inductive load turn-off Non-repetitive clamping energy	$I_{DM} = 8\text{ A}; V_{DD} \leq 20\text{ V}$ $T_{mb} \leq 25\text{ °C}$	-	100	mJ
E_{DRM}	Repetitive clamping energy	$T_{mb} \leq 95\text{ °C}; f = 250\text{ Hz}$	-	20	mJ

OVERLOAD PROTECTION LIMITING VALUE

With an adequate protection supply provided via the input pin, TOPFET can protect itself from two types of overload - overtemperature and short circuit load.

SYMBOL	PARAMETER	REQUIRED CONDITION	MIN.	MAX.	UNIT
V_{DS}	Drain source voltage ³	$4\text{ V} \leq V_{IS} \leq 5.5\text{ V}$	0	35	V

THERMAL CHARACTERISTIC

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance Junction to mounting base	-	-	2.5	3.1	K/W

¹ Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.

² A higher T_j is allowed as an overload condition but at the threshold $T_{j(TO)}$ the over temperature trip operates to protect the switch.

³ All control logic and protection functions are disabled during conduction of the source drain diode.

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BUK117-50DL

OUTPUT CHARACTERISTICS

Limits are for $-40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$; typicals are for $T_{\text{mb}} = 25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(\text{CL})\text{DSS}}$	Off-state Drain-source clamping voltage	$V_{\text{IS}} = 0\text{ V}$				
		$I_{\text{D}} = 10\text{ mA}$	50	-	-	V
I_{DSS}	Drain source leakage current	$I_{\text{DM}} = 1\text{ A}; t_{\text{p}} \leq 300\text{ }\mu\text{s}; \delta \leq 0.01$	50	60	70	V
		$V_{\text{DS}} = 40\text{ V}$ $T_{\text{mb}} = 25^{\circ}\text{C}$	-	-	100	μA
$R_{\text{DS(ON)}}$	On-state Drain-source resistance	$I_{\text{DM}} = 3\text{ A}; t_{\text{p}} \leq 300\text{ }\mu\text{s}; \delta \leq 0.01$				
		$V_{\text{IS}} \geq 4.4\text{ V}$ $T_{\text{mb}} = 25^{\circ}\text{C}$	-	-	190	$\text{m}\Omega$
			-	68	100	$\text{m}\Omega$
		$V_{\text{IS}} \geq 4\text{ V}$ $T_{\text{mb}} = 25^{\circ}\text{C}$	-	-	200	$\text{m}\Omega$
			-	72	105	$\text{m}\Omega$

OVERLOAD CHARACTERISTICS

 $-40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{D}	Short circuit load Drain current limiting	$V_{\text{DS}} = 13\text{ V}$				
		$V_{\text{IS}} = 5\text{ V}; T_{\text{mb}} = 25^{\circ}\text{C}$	8	12	16	A
		$4.4\text{ V} \leq V_{\text{IS}} \leq 5.5\text{ V}$	6	-	18	A
		$4\text{ V} \leq V_{\text{IS}} \leq 5.5\text{ V}$	5	-	18	A
$P_{\text{D(TO)}}$ T_{DSC}	Overload protection Overload power threshold Characteristic time	$V_{\text{IS}} = 5\text{ V}; T_{\text{mb}} = 25^{\circ}\text{C}$				
		device trips if $P_{\text{D}} > P_{\text{D(TO)}}$ which determines trip time ¹	20 200	55 350	80 600	W μs
$T_{\text{j(TO)}}$	Overtemperature protection Threshold junction temperature ²		150	170	-	$^{\circ}\text{C}$

¹ Trip time t_{dsc} varies with overload dissipation P_{D} according to the formula $t_{\text{dsc}} \approx T_{\text{DSC}} / \ln[P_{\text{D}} / P_{\text{D(TO)}}]$.

² This is independent of the dV/dt of input voltage V_{IS} .

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BUK117-50DL

INPUT CHARACTERISTICS

The supply for the logic and overload protection is taken from the input.

Limits are for $-40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$; typicals are for $T_{\text{mb}} = 25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{\text{IS(TO)}}$	Input threshold voltage	$V_{\text{DS}} = 5 \text{ V}$; $I_{\text{D}} = 1 \text{ mA}$ $T_{\text{mb}} = 25^{\circ}\text{C}$	0.6	-	2.4	V
			1.1	1.6	2.1	V
I_{IS}	Input supply current	normal operation; $V_{\text{IS}} = 5 \text{ V}$ $V_{\text{IS}} = 4 \text{ V}$	100	220	400	μA
			80	195	330	μA
I_{ISL}	Input supply current	protection latched; $V_{\text{IS}} = 5 \text{ V}$ $V_{\text{IS}} = 3 \text{ V}$	200	400	650	μA
			130	250	430	μA
V_{ISR}	Protection reset voltage ¹	reset time $t_{\text{r}} \geq 100 \mu\text{s}$	1.5	2	2.9	V
t_{lr}	Latch reset time	$V_{\text{IS1}} = 5 \text{ V}$, $V_{\text{IS2}} < 1 \text{ V}$	10	40	100	μs
$V_{\text{(CL)IS}}$	Input clamping voltage	$I_{\text{I}} = 1.5 \text{ mA}$	5.5	-	8.5	V
R_{IG}	Input series resistance ² to gate of power MOSFET	$T_{\text{mb}} = 25^{\circ}\text{C}$	-	33	-	$\text{k}\Omega$

SWITCHING CHARACTERISTICS

$T_{\text{mb}} = 25^{\circ}\text{C}$; $V_{\text{DD}} = 13 \text{ V}$; resistive load $R_{\text{L}} = 4 \Omega$. Refer to waveform figure and test circuit.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{don}	Turn-on delay time	$V_{\text{IS}} = 5 \text{ V}$	-	10	20	μs
t_{r}	Rise time		-	20	40	μs
t_{doff}	Turn-off delay time	$V_{\text{IS}} = 0 \text{ V}$	-	30	60	μs
t_{f}	Fall time		-	20	40	μs

¹ The input voltage below which the overload protection circuits will be reset.

² Not directly measureable from device terminals.

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MECHANICAL DATA

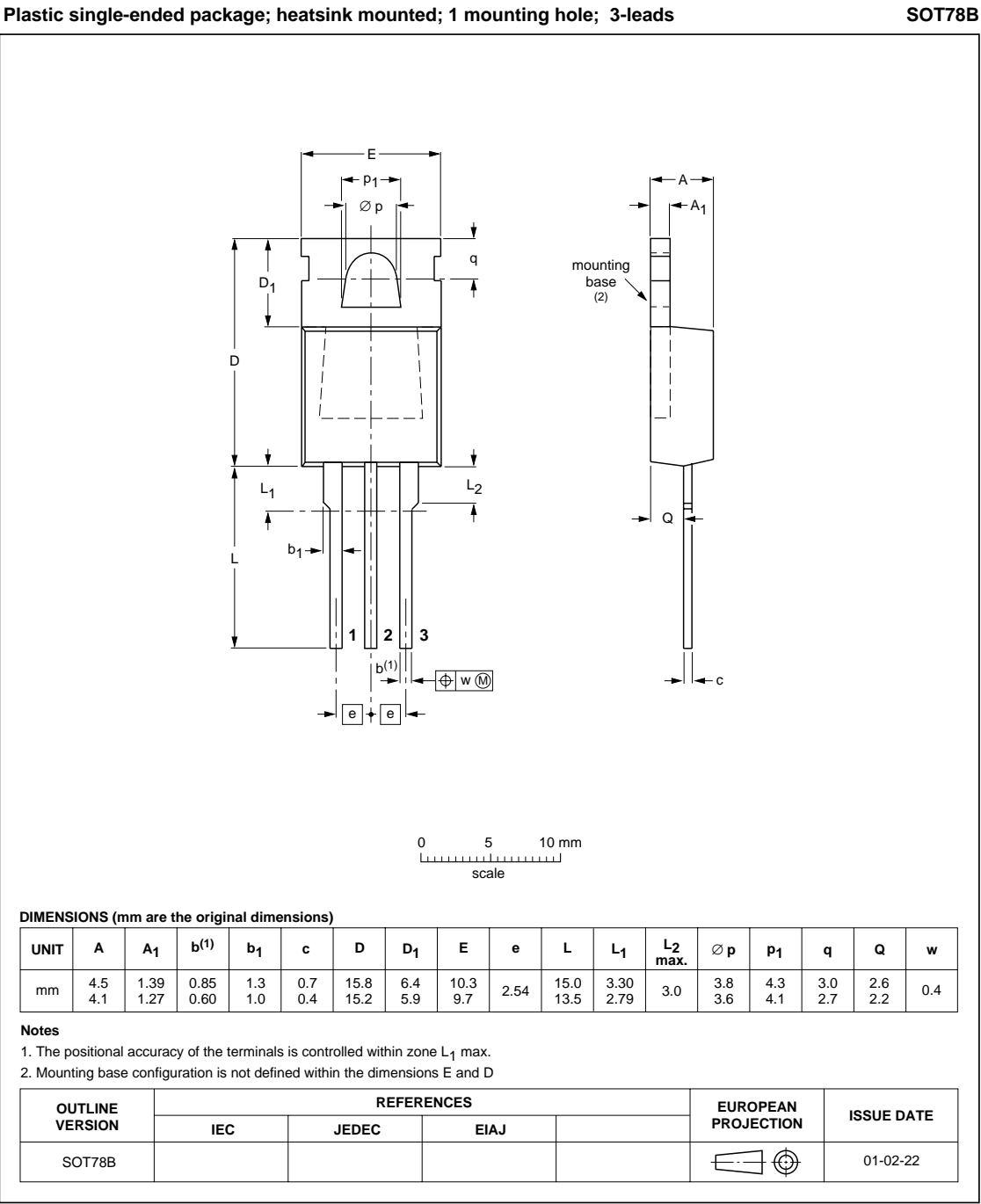


Fig.2. SOT78B (TO220AB) package¹, pin 2 connected to mounting base.

¹ Refer to mounting instructions for SOT78 (TO220) envelopes. Epoxy meets UL94 V0 at 1/8". Net mass: 2 g

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BUK117-50DL

DEFINITIONS

DATA SHEET STATUS		
DATA SHEET STATUS ¹	PRODUCT STATUS ²	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A
Limiting values		
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		
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